

TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process)

HN1B26FS

General-Purpose Amplifier Applications

Unit: mm

Q1

· High voltage and high current

: $V_{CEO} = 50 \text{ V}$, $I_{C} = 100 \text{ mA (max)}$

• Excellent hee linearity: hee (IC = 0.1 mA)/hee (IC = 2 mA) = 0.95 (typ.)

• High h_{FE} : h_{FE} = 120~400

Q2

High voltage and high current

 $: V_{CEO} = -50 \text{ V}, I_{C} = -100 \text{ mA (max)}$

Excellent he linearity:

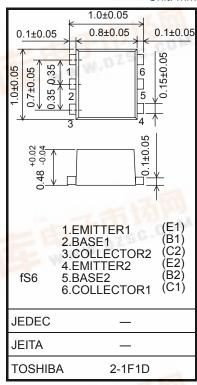
Total rating

 $h_{FE} (I_C = -0.1 \text{ mA})/h_{FE} (I_C = -2 \text{ mA}) = -0.95 \text{ (typ.)}$

• High hff $h_{FF} = 120 \sim 400$

Q1 Absolute Maximum Ratings (Ta = 25°C)

| Characteristic | Symbol | Rating | Unit |
|---------------------------|------------------|--------|------|
| Collector-base voltage | V _{CBO} | 60 | V |
| Collector-emitter voltage | V _{CEO} | 50 | V |
| Emitter-base voltage | V _{EBO} | 5 | V |
| Collector current | IC | 100 | mA |
| Base current | ΙΒ | 30 | mA |



Weight: 0.0008 g (typ.)

Q2 Absolute Maximum Ratings (Ta = 25°C)

| Characteristic | Symbol | Rating | Unit |
|---------------------------|------------------|--------|------|
| Collector-base voltage | V _{CBO} | -50 | V |
| Collector-emitter voltage | V _{CEO} | -50 | V |
| Emitter-base voltage | V _{EBO} | -5 | V |
| Collector current | IC | -100 | mA |
| Base current | ΙΒ | -30 | mA |

Q1, Q2 Common Absolute Maximum Ratings (Ta = 25°C)

| Characteristic | Symbol | Rating | Unit |
|-----------------------------|------------------|---------|------|
| Collector power dissipation | PC | 50* | mW |
| Junction temperature | T _j | 150 | °C |
| Storage temperature range | T _{stg} | -55~150 | °C |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Q1 Electrical Characteristics (Ta = 25°C)

| Characteristic | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------------|------------------------|---|-----|------|------|------|
| Collector cutoff current | I _{CBO} | V _{CB} = 60 V, I _E = 0 | _ | _ | 0.1 | μА |
| Emitter cutoff current | I _{EBO} | V _{EB} = 5 V, I _C = 0 | _ | _ | 0.1 | μΑ |
| DC current gain | h _{FE} (Note) | $V_{CE} = 6 \text{ V}, I_{C} = 2 \text{ mA}$ | 120 | _ | 400 | |
| Collector-emitter saturation voltage | V _{CE (sat)} | $I_C = 100 \text{ mA}, I_B = 10 \text{ mA}$ | | 0.1 | 0.25 | > |
| Transition frequency | f _T | V _{CE} = 10 V, I _C = 1 mA | 60 | _ | | MHz |
| Collector output capacitance | C _{ob} | $V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$ | _ | 0.95 | _ | pF |

Q2 Electrical Characteristics (Ta = 25°C)

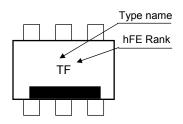
| Characteristic | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------------|------------------------|--|-----|-------|------|------|
| Collector cutoff current | I _{CBO} | $V_{CB} = -50 \text{ V}, I_E = 0$ | _ | _ | -0.1 | μА |
| Emitter cutoff current | I _{EBO} | $V_{EB} = -5 \text{ V}, I_C = 0$ | _ | _ | -0.1 | μА |
| DC current gain | h _{FE} (Note) | $V_{CE} = -6 \text{ V}, I_{C} = -2 \text{ mA}$ | 120 | _ | 400 | _ |
| Collector-emitter saturation voltage | V _{CE} (sat) | $I_C = -100 \text{ mA}, I_B = -10 \text{ mA}$ | _ | -0.18 | -0.3 | ٧ |
| Transition frequency | f _T | $V_{CE} = -10 \text{ V}, I_{C} = -1 \text{ mA}$ | 80 | | | MHz |
| Collector output capacitance | C _{ob} | $V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$ | _ | 1.6 | _ | pF |

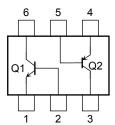
Note: hFE classification Y (F): 120~240, GR (H): 200~400

() marking symbol

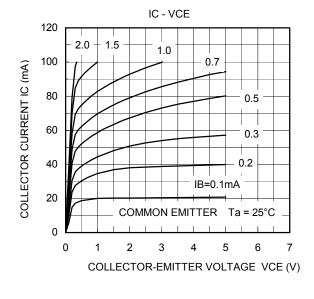
Marking (top view)

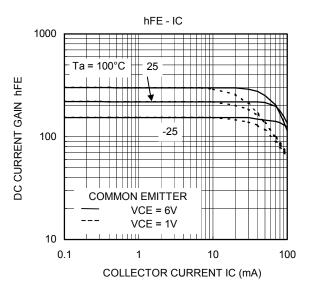
Equivalent Circuit

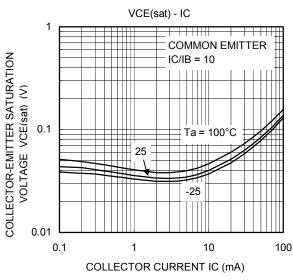


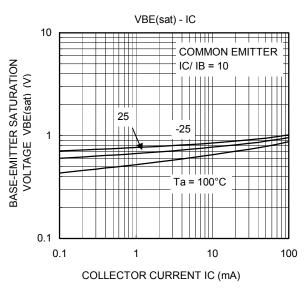


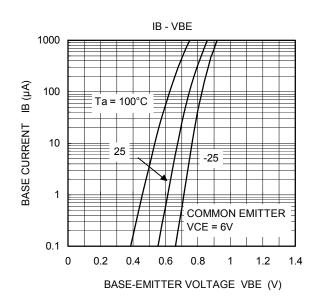
Q1





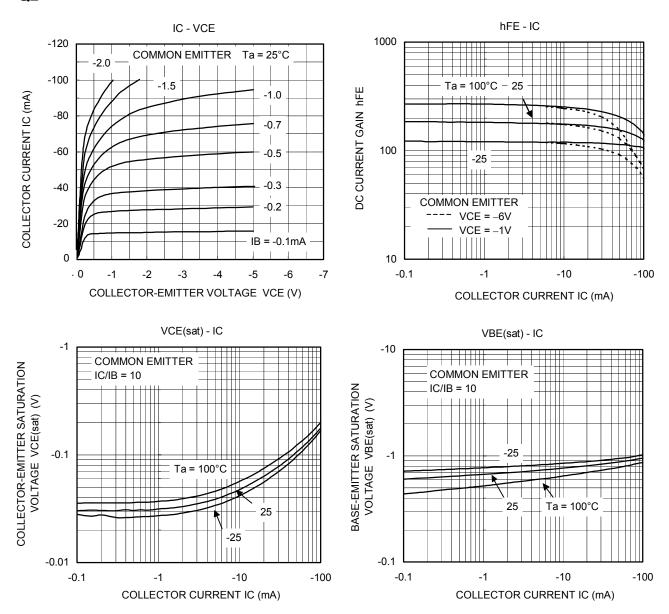


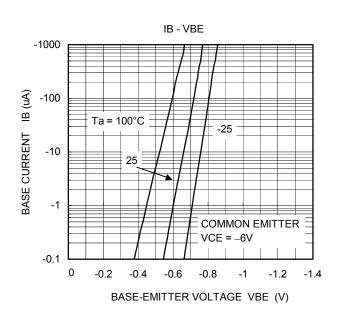




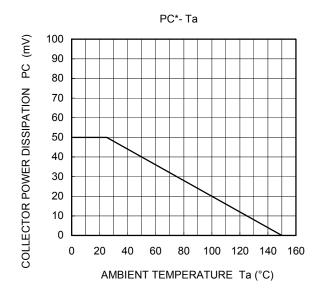
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Q2





Q1, Q2 COMMON



*: Total rating

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20070701-EN GENERAL

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